

1. General description

WSJM65R600X is a high voltage N-channel MOSFET in TO220F package, which utilizes the advanced super-junction technology to provide superior FOM $R_{DS(on)} * Q_g$ among silicon based MOSFETs. It is particularly suitable for applications require extreme high efficiency and power density.



2. Features and benefits

- Superior FOM $R_{DS(on)} * Q_g$
- Extremely low switching loss
- 100% avalanche tested

3. Applications

- Chargers
- Adapters
- Lighting
- Flyback topologies for high efficiency power supplies

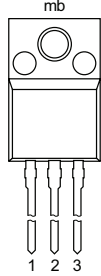
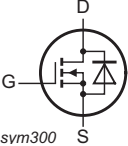
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{DS}	drain-source voltage			650			V
V_{GS}	gate-source voltage			±30			V
I_D	continuous drain current	$T_h = 25\text{ °C}$	[1]	8.0			A
P_{tot}	power dissipation	$T_h = 25\text{ °C}$		28			W
T_j	junction temperature			-55 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$		-	522	600	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 3.5\text{ A}; V_{DS} = 400\text{ V}; V_{GS} = 10\text{ V}$		-	12	-	nC
E_{OSS}	coss stored energy	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V}$		-	1.8	-	μJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WSJM65R600X	TO220F	WSJM65R600XQ	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
WSJM65R600X	WSJM 65R600X

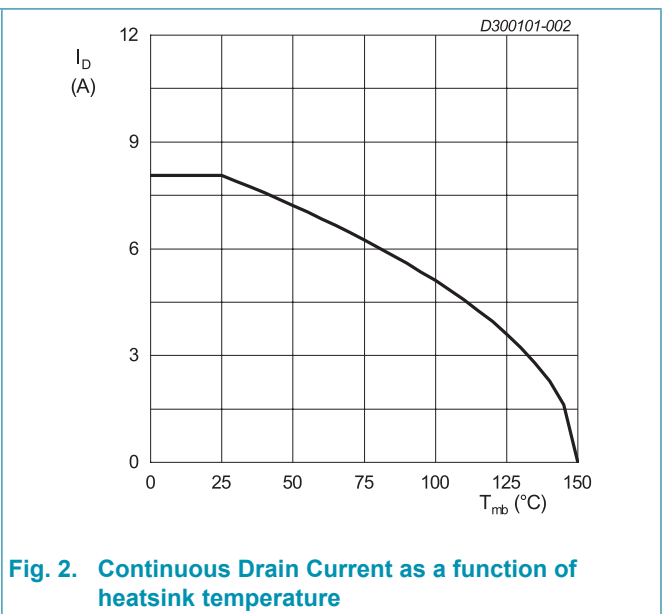
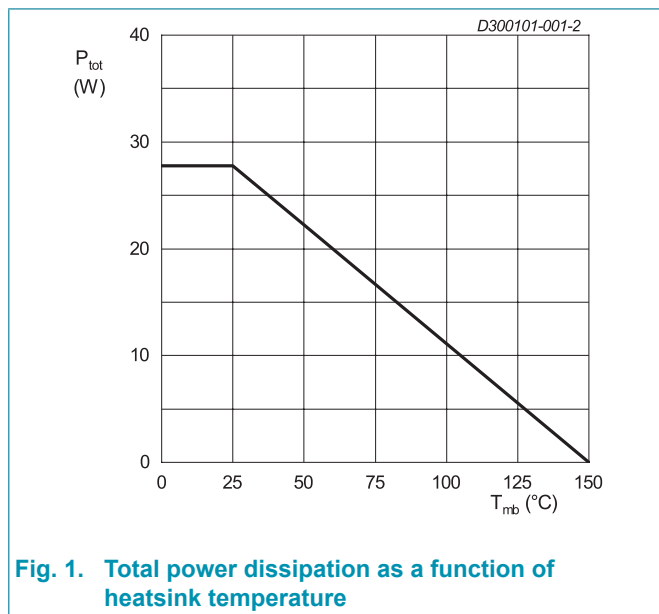
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DS}	drain-source voltage			650	V
V_{GS}	gate-source voltage			± 30	V
I_D	continuous drain current	$T_h = 25\text{ }^\circ\text{C}$	[1]	8.0	A
		$T_h = 100\text{ }^\circ\text{C}$	[1]	5.1	A
I_{DM}	pulsed drain current	$T_h = 25\text{ }^\circ\text{C}$		22	A
P_{tot}	power dissipation	$T_h = 25\text{ }^\circ\text{C}$		28	W
E_{AS}	single pulse drain-to-source avalanche	$I_{AS} = 2.1\text{ A}$; $R_{GS} = 25\text{ }\Omega$; $V_{DD} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$		22	mJ
E_{AR}	repetitive avalanche energy	$I_{AS} = 2.1\text{ A}$; $R_{GS} = 25\text{ }\Omega$; $V_{DD} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$		0.5	mJ
I_{AS}	avalanche current, single pulse			2.1	A
dv/dt	MOSFET dv/dt ruggedness			50	V/ns
dv/dt	reverse diode dv/dt			15	V/ns
dI _r /dt	maximum diode commutation speed			500	A/ μ s
T_{stg}	storage temperature			-55 to 150	$^\circ\text{C}$
T_j	junction temperature			-55 to 150	$^\circ\text{C}$

[1] Limited by maximum junction temperature, equivalent to TO220.



9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink			-	3.6	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

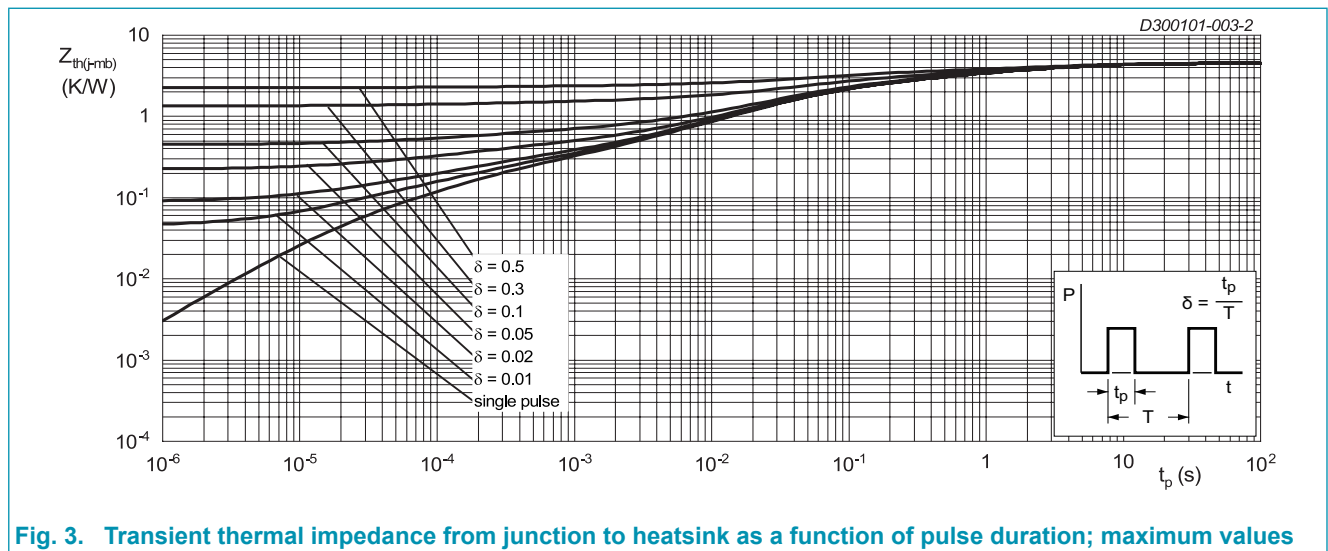


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}$		650	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\ \mu\text{A}; V_{DS} = V_{GS}$		2.5	-	4.5	V
I_{DSS}	drain leakage current	$V_{DS} = 650\ \text{V}; V_{GS} = 0\ \text{V}$		-	-	1	μA
		$V_{DS} = 650\ \text{V}; V_{GS} = 0\ \text{V}; T_j = 125\text{ }^\circ\text{C}$		-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = \pm 30\ \text{V}; V_{DS} = 0\ \text{V}$		-	-	± 100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}; I_D = 3.5\ \text{A}$		-	522	600	m Ω
R_G	gate resistance	$f = 1\ \text{MHz}$		-	8.5	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 3.5\ \text{A}; V_{DS} = 400\ \text{V}; V_{GS} = 10\ \text{V}$		-	12	-	nC
Q_{GS}	gate-source charge			-	2.6	-	nC
Q_{GD}	gate-drain charge			-	5.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 400\ \text{V}; V_{GS} = 0\ \text{V}; f = 1\ \text{MHz}$		-	520	-	pF
C_{oss}	output capacitance			-	16	-	pF
C_{rss}	reverse transfer capacitance			-	2.6	-	pF
$C_{o(er)}$	effective output capacitance, energy related	$V_{GS} = 0\ \text{V}; V_{DS} = 0\ \text{to}\ 400\ \text{V}$		-	22	-	pF
$C_{o(tr)}$	effective output capacitance, time related			-	90	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 400\ \text{V}; V_{GS} = 10\ \text{V}; R_G = 2\ \Omega;$ $I_D = 3.5\ \text{A}$		-	18	-	ns
t_r	rise time			-	14	-	ns
$t_{d(off)}$	turn-off delay time			-	30	-	ns
t_f	fall time			-	16	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	$V_{GS} = 0\ \text{V}; I_S = 3.5\ \text{A}$		-	0.8	1.1	V
I_S	body-diode continuous current	$T_h = 25\text{ }^\circ\text{C}$		-	-	8.0	A
t_{rr}	reverse recovery time	$V_R = 400\ \text{V}; I_F = 3.5\ \text{A}; di_F/dt = 100\ \text{A}/\mu\text{s}$		-	182	-	ns
Q_{rr}	reverse recovered charge			-	1.5	-	μC
I_{rrm}	reverse recovery current			-	15	-	A

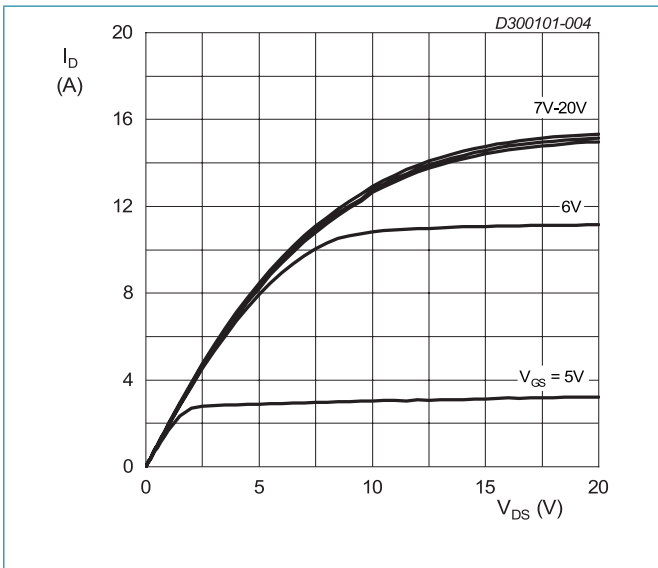
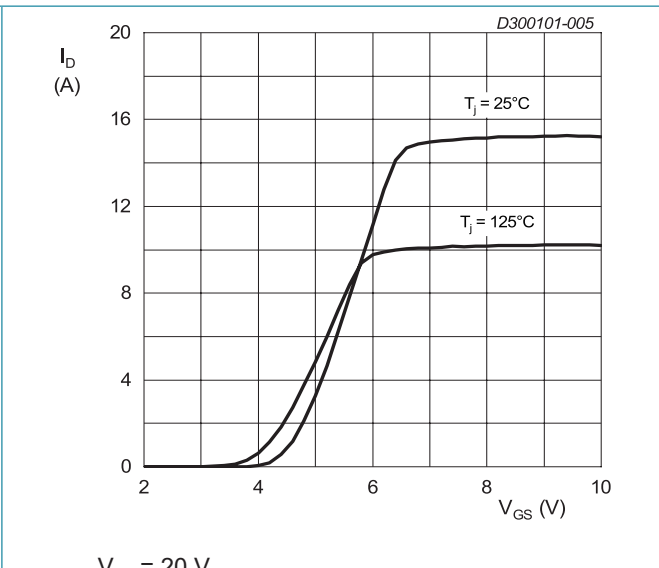
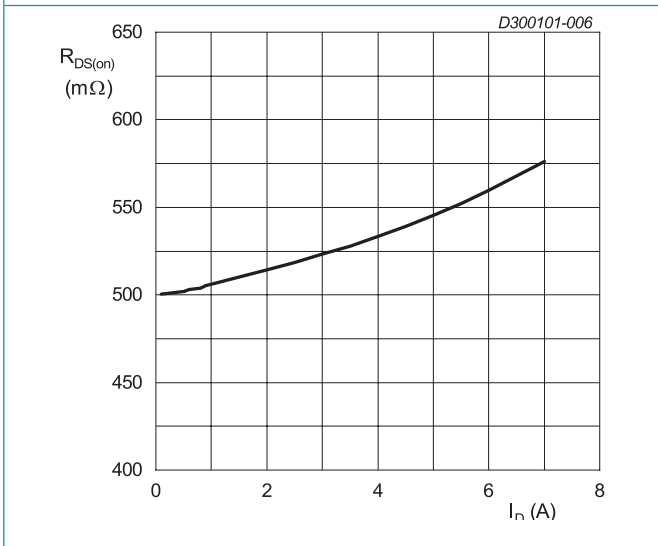


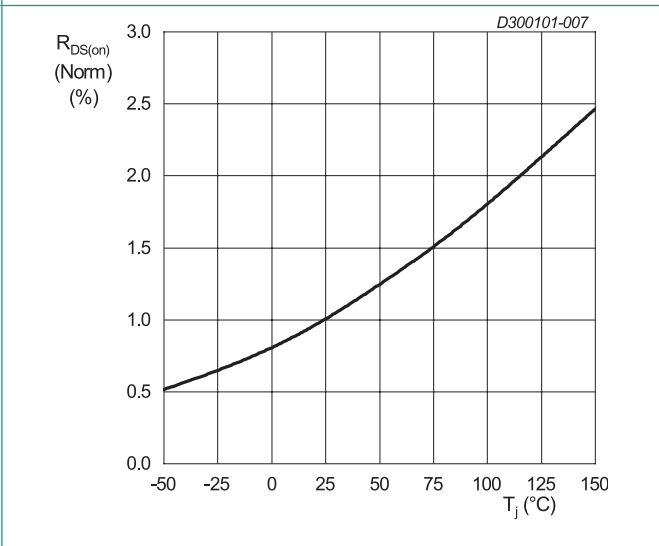
Fig. 4. Drain current as a function of drain-source voltage; typical values



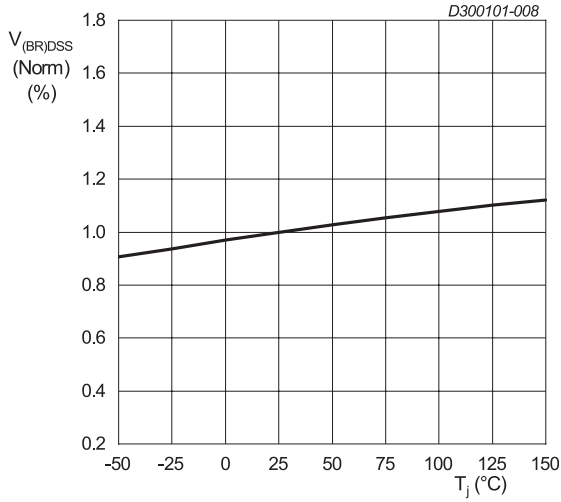
$V_{DS} = 20\text{ V}$
Fig. 5. Drain current as a function of gate-source voltage; typical values



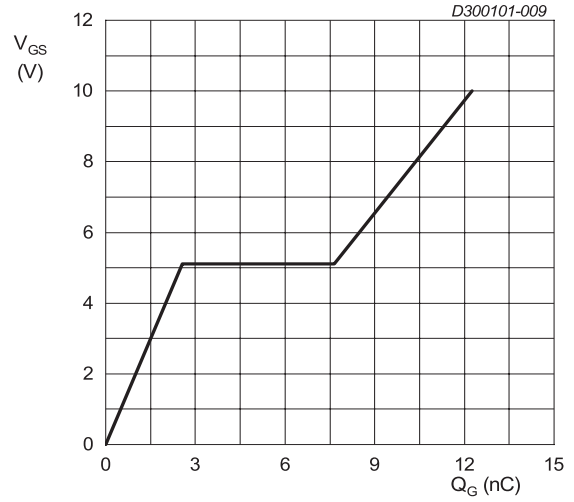
$V_{GS} = 10\text{ V}$
Fig. 6. Drain-source on-state resistance as a function of drain current; typical values



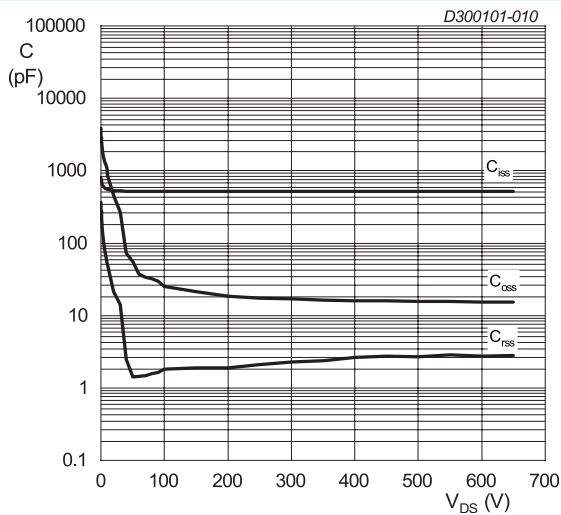
$V_{GS} = 10\text{ V}; I_D = 3.5\text{ A}$
Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



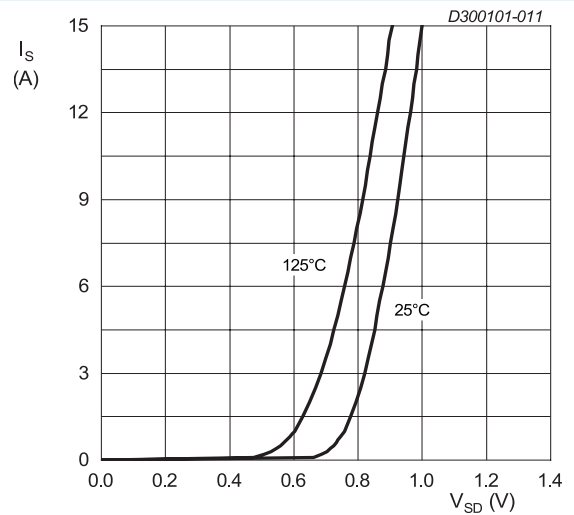
$I_D = 250 \mu A$
Fig. 8. Normalized drain-source breakdown voltage as a function of junction temperature



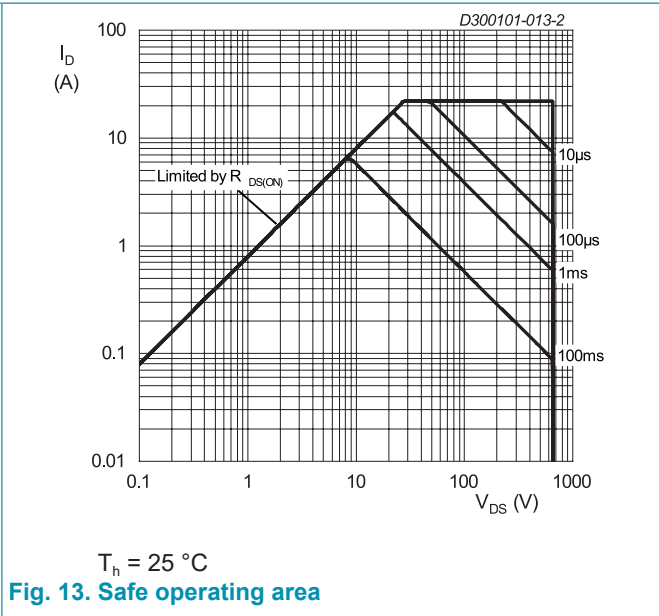
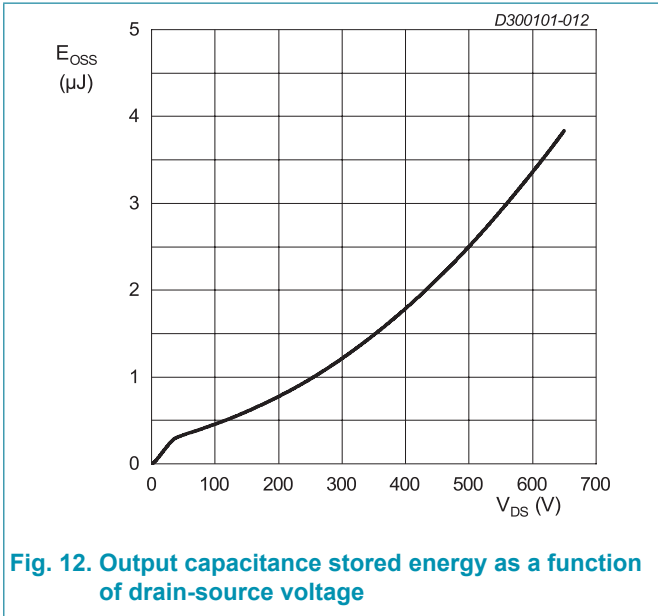
$I_D = 3.5 A; V_{DS} = 400 V$
Fig. 9. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 V; f = 1 MHz$
Fig. 10. Capacitances as a function of drain-source voltage; typical values



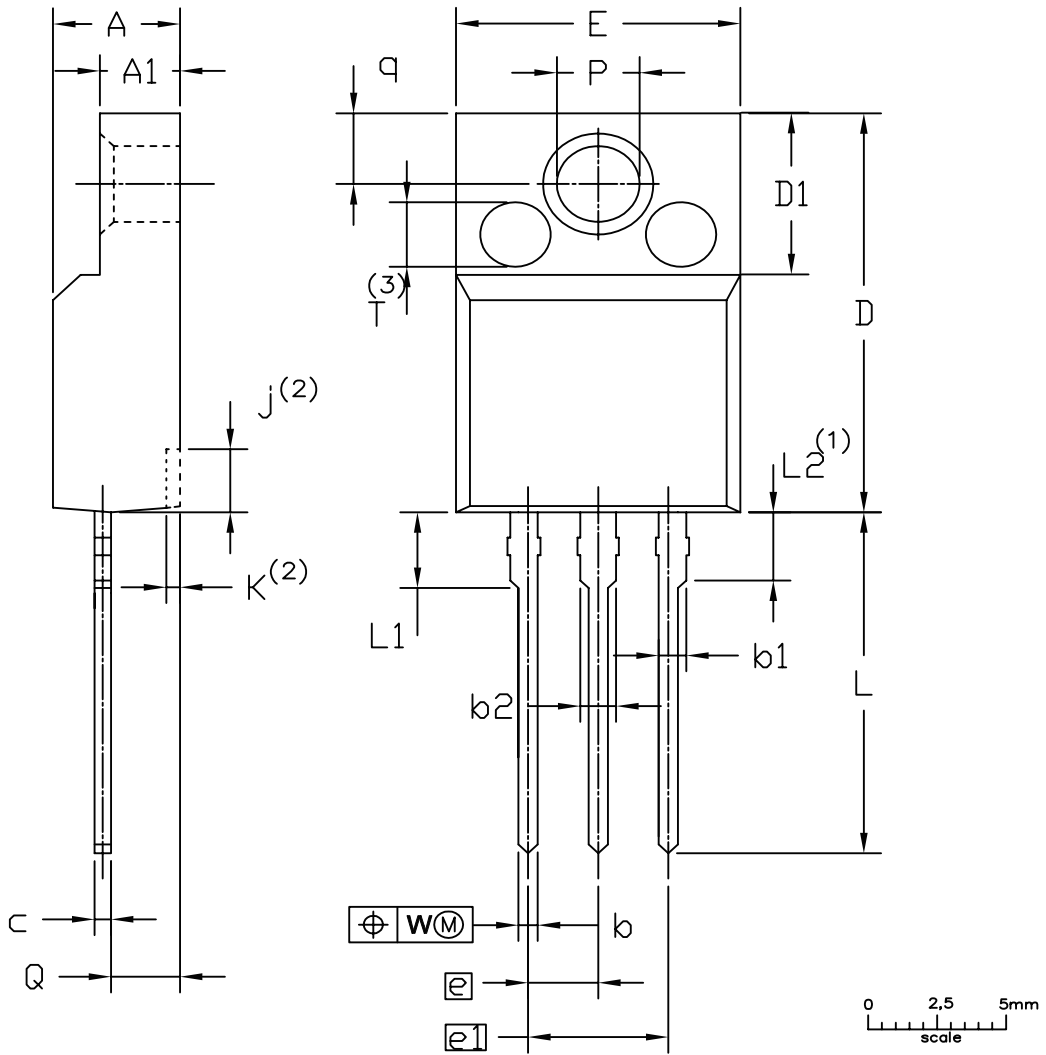
$V_{GS} = 0 V$
Fig. 11. Source current as a function of source-drain voltage; typical values



11. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁	E	e	e ₁	j ⁽²⁾	k ⁽²⁾	L	L ₁	L ₂ ⁽¹⁾ max.	P	Q	q	W	T ⁽³⁾
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3			2.7	0.6	14.4	3.30		3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7	2.54	5.08	1.7	0.4	13.5	2.79	3	3.0	2.3	2.6		

Notes

- 1. Terminal dimensions within this zone are uncontrolled
- 2. Dot lines area designs may vary
- 3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3 LEADS TO220F			2013-11-14

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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